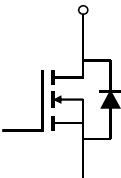


100V 2.8m N-Ch Power MOSFET

Features

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th_Typ)}$	2.7	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	196	A
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 10V$)	2.8	m



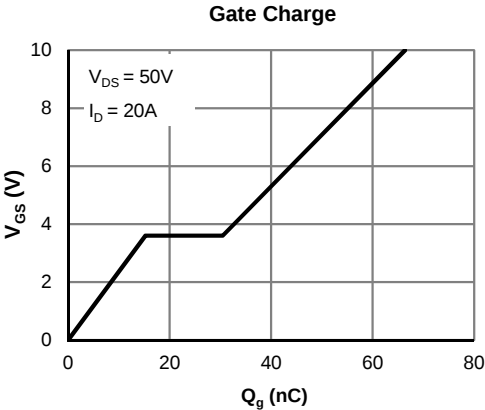
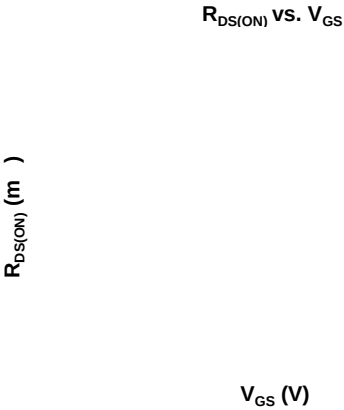
Rev. 1.1

Ordering Information

Device	Package	# of Pins	Marking	MSL	T _J (°C)	Media	Quantity (pcs)
JMSH1003AE7Q-13	TO-263-7L	7	SH1003AQ	1	-55 to 175	13-inch Reel	800

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	±20	V
			A
	I_{DM}		A
Avalanche Current ⁽³⁾	I_{AS}	52	A
Avalanche Energy ⁽³⁾	E_{AS}	406	mJ
Power Dissipation ⁽⁴⁾	P_D	283	W
		142	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

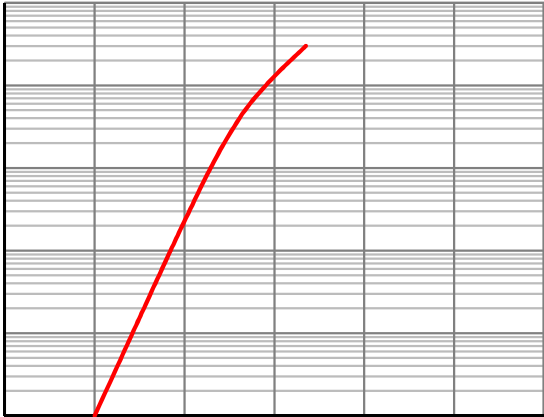




	Symbol	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{(BR)DSS}$	100			V
	$V_{DS} = 80V, V_{GS} = 0V$			1.0	
	$T_J = 55^{\circ}C$			5.0	
	I_{GSS}			±100	nA
	$V_{GS(th)}$	2.0	2.7	4.0	V
	$R_{DS(on)}$		2.8	3.5	m
	g_{FS}		85		S
	V_{SD}		0.71	1.0	V
	I_S			283	A
	C_{iss}		4398		pF
	C_{oss}		1361		pF
	C_{rss}		8.5		pF
	R_g		2.5		
	Q_g		66		nC
	Q_g		44		nC
	Q_{gs}		15.2		nC
	Q_{gd}		15.2		nC
	$t_{D(on)}$		17.2		ns
	t				



Typical Electrical & Thermal Characteristics





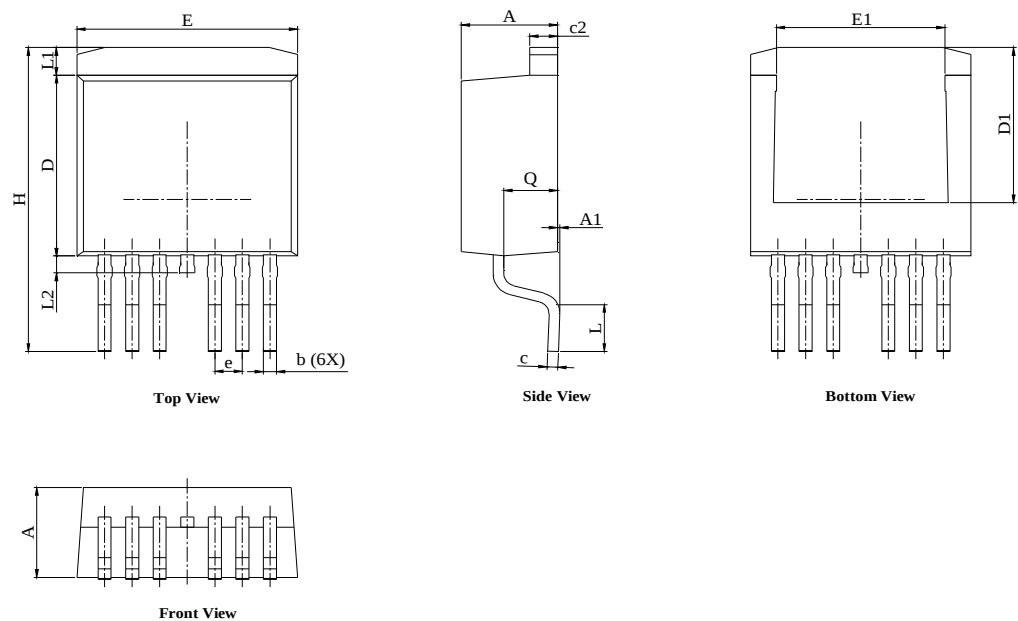
JMSH1003AE7Q

Typical Electrical & Thermal Characteristics



TO-263-7L Package Information

Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	7.65 REF.		
E	9.96	10.16	10.36
E1	6.80	7.80	8.00
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.80
L1		1.36 REF.	
L2		1.20 REF.	
L3		0.25 BSC	
Q	2.30	2.48	2.70

Recommended Soldering Footprint

